

8-Bit Serial-Input/Parallel-Output Shift Register

MC74HC164B

High-Performance Silicon-Gate CMOS

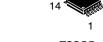
The MC74HC164B is identical in pinout to the LS164. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The MC74HC164B is an 8-bit, serial-input to parallel-output shift register. Two serial data inputs, A1 and A2, are provided so that one input may be used as a data enable. Data is entered on each rising edge of the clock. The active-low asynchronous Reset overrides the Clock and Serial Data inputs. Schmitt-trigger action at the Clock input enhances the device's tolerance to slower rise and fall times and immunity to noise of the input clock signal.

Features

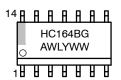
- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 V to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7 A Requirements
- Chip Complexity: 244 FETs or 61 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant





SOIC-14 D SUFFIX CASE 751A TSSOP-14 DT SUFFIX CASE 948G

MARKING DIAGRAM





= Assembly Location

L, WL = Wafer Lot Y = Year W, WW = Work Week G or ■ = Pb-Free Package

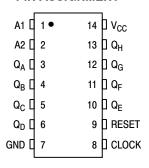
(Note: Microdot may be in either location)

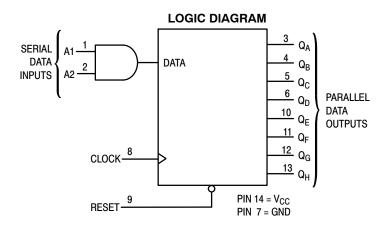
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NOTE: Some of the device on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2

PIN ASSIGNMENT





FUNCTION TABLE

Inputs					Outp	outs	
Reset	Clock	A 1	A2	Q_A	Q_{B}		Q_{H}
L	Х	Х	Х	L	L		L
Н	~	Х	Χ	1	No Ch	ang	е
Н		Н	D	D	Q_{An}		Q_{Gn}
Н	\	D	Н	D	Q_{An}	•••	Q_{Gn}

D = data input

 Q_{An} – Q_{Gn} = data shifted from the preceding stage on a rising edge at the clock input.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC164BDR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel

DISCONTINUED (Note 1)

Device	Package	Shipping [†]
MC74HC164BDG	SOIC-14	55 Units / Rail
NLV74HC164BDR2G*	(Pb-Free)	2500 / Tape & Reel
MC74HC164BDTR2G	TSSOP-14	2500 / Tape & Reel
NLV74HC164BDTR2G*	(Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	±[2 0	mA
I _{out}	DC Output Current, per Pin	±[2 5	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±[5 0	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating — SOIC Package: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			V _{CC}	V
T _A	Operating Temperature, All Package Types		– 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	No Limit No Limit No Limit	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC} V	-55°C to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{T+} max	Maximum Positive-Going Input Threshold Voltage (Figure 3)	V _{out} = 0.1V I _{out} ≤ 20μA	2.0 3.0 4.5 6.0	1.50 2.15 3.15 4.20	1.50 2.15 3.15 4.20	1.50 2.15 3.15 4.20	V
V _{T+} min	Minimum Positive-Going Input Threshold Voltage (Figure 3)	V _{out} = 0.1V I _{out} ≤ 20μA	2.0 3.0 4.5 6.0	1.0 1.5 2.3 3.0	0.95 1.45 2.25 2.95	0.95 1.45 2.25 2.95	V
V _{T-} max	Maximum Negative-Going Input Threshold Voltage (Figure 3)	$V_{out} = V_{CC} - 0.1V$ $ I_{out} \le 20\mu A$	2.0 3.0 4.5 6.0	0.9 1.4 2.0 2.6	0.95 1.45 2.05 2.65	0.95 1.45 2.05 2.65	V
V _{T-} min	Minimum Negative-Going Input Threshold Voltage (Figure 3)	$V_{out} = V_{CC} - 0.1V$ $ I_{out} \le 20\mu A$	2.0 3.0 4.5 6.0	0.3 0.5 0.9 1.2	0.3 0.5 0.9 1.2	0.3 0.5 0.9 1.2	V
V _H max (Note 2)	Maximum Hysteresis Voltage (Figure 3)	$V_{out} = 0.1V \text{ or } V_{CC} - 0.1V$ $ I_{out} \le 20\mu\text{A}$	2.0 3.0 4.5 6.0	1.20 1.65 2.25 3.00	1.20 1.65 2.25 3.00	1.20 1.65 2.25 3.00	V
V _H min (Note 2)	Minimum Hysteresis Voltage (Figure 3)	$V_{out} = 0.1V \text{ or } V_{CC} - 0.1V$ $ I_{out} \le 20\mu\text{A}$	2.0 3.0 4.5 6.0	0.20 0.25 0.40 0.50	0.20 0.25 0.40 0.50	0.20 0.25 0.40 0.50	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{aligned} V_{in} = V_{IH} \text{ or } V_{IL} & & I_{out} \leq 2.4 \text{ mA} \\ & & I_{out} \leq 4.0 \text{ mA} \\ & & I_{out} \leq 5.2 \text{ mA} \end{aligned}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{aligned} V_{in} = V_{IH} \text{ or } V_{IL} & & I_{out} \leq 2.4 \text{ mA} \\ & I_{out} \leq 4.0 \text{ mA} \\ & I_{out} \leq 5.2 \text{ mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±[0.1	±∏1.0	±[1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. $V_H min > (V_{T_+} min) - (V_{T_-} max); V_H max = (V_{T_+} max) - (V_{T_-} min).$

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_{\rm f}$ = $t_{\rm f}$ = 6 ns)

			Guaranteed Limit			
Symbol	Parameter	V _{CC}	–55°C to 25°C	≤ 85 °C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle)	2.0	10	10	10	MHz
	(Figures 1 and 4)	3.0	20	20	20	
		4.5	40	35	30	
		6.0	50	45	40	
t _{PLH} ,	Maximum Propagation Delay, Clock to Q	2.0	160	200	250	ns
t _{PHL}	(Figures 1 and 4)	3.0	100	150	200	
		4.5	32	40	48	
		6.0	27	34	42	
t _{PHL}	Maximum Propagation Delay, Reset to Q	2.0	175	220	260	ns
	(Figures 2 and 4)	3.0	100	150	200	
		4.5	35	44	53	
		6.0	30	37	45	
t _{TLH} ,	Maximum Output Transition Time, Any Output	2.0	75	95	110	ns
t _{THL}	(Figures 1 and 4)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
C _{in}	Maximum Input Capacitance	_	10	10	10	pF
			T - · ·	⊕ oe°C V	F O V	

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Package)*	180	pF

TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

			Gu	aranteed Li	mit	
Symbol	Parameter	V _{CC} V	–55°C to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{su}	Minimum Setup Time, A1 or A2 to Clock (Figure 3)	2.0 3.0 4.5 6.0	25 15 7 5	35 20 8 6	40 25 9 6	ns
t _h	Minimum Hold Time, Clock to A1 or A2 (Figure 3)	2.0 3.0 4.5 6.0	3 3 3 3	3 3 3 3	3 3 3 3	ns
t _{rec}	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0 3.0 4.5 6.0	3 3 3 3	3 3 3 3	3 3 3 3	ns
t _w	Minimum Pulse Width, Clock (Figure 1)	2.0 3.0 4.5 6.0	50 26 12 10	60 35 15 12	75 45 20 15	ns
t _w	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	50 26 12 10	60 35 15 12	75 45 20 15	ns

PIN DESCRIPTIONS

INPUTS

A1, A2 (Pins 1, 2)

Serial Data Inputs. Data at these inputs determine the data to be entered into the first stage of the shift register. For a high level to be entered into the shift register, both A1 and A2 inputs must be high, thereby allowing one input to be used as a data–enable input. When only one serial input is used, the other must be connected to $V_{\rm CC}$.

Clock (Pin 8)

Shift Register Clock. A positive-going transition on this pin shifts the data at each stage to the next stage. The shift

register is completely static, allowing clock rates down to DC in a continuous or intermittent mode.

OUTPUTS

Q_A - Q_H (Pins 3, 4, 5, 6, 10, 11, 12, 13)

Parallel Shift Register Outputs. The shifted data is presented at these outputs in true, or noninverted, form.

CONTROL INPUT

Reset (Pin 9)

Active–Low, Asynchronous Reset Input. A low voltage applied to this input resets all internal flip–flops and sets Outputs Q_A – Q_H to the low level state.

SWITCHING WAVEFORMS

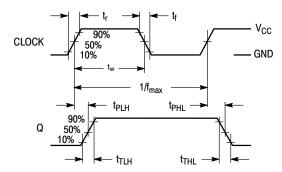


Figure 1.

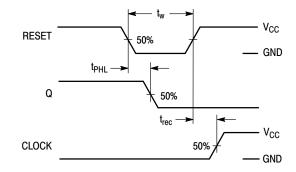


Figure 2.

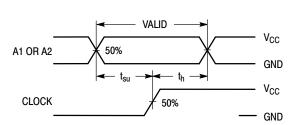
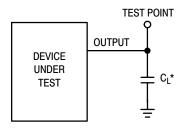


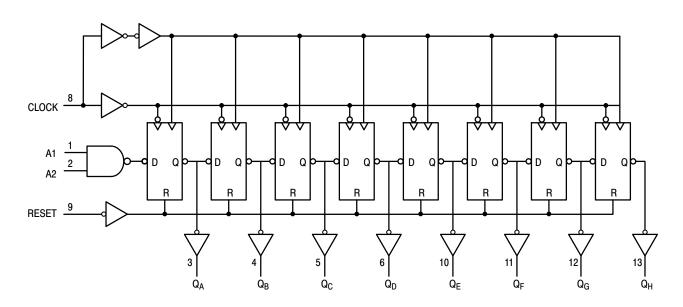
Figure 3.



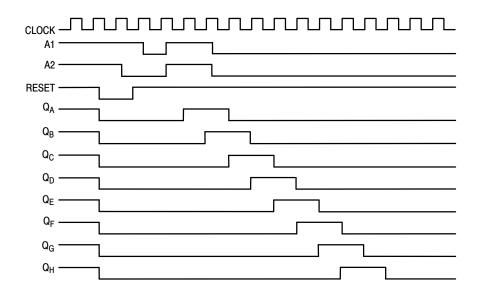
*Includes all probe and jig capacitance

Figure 4. Test Circuit

EXPANDED LOGIC DIAGRAM



TIMING DIAGRAM



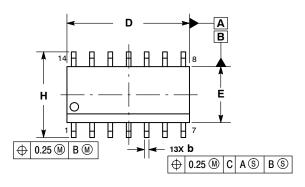


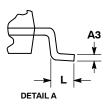


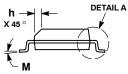
△ 0.10

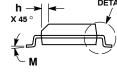
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DATE 03 FEB 2016





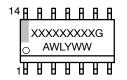




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
 - MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
œ	1.27	BSC	0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

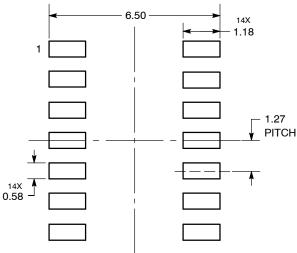
WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*

C SEATING PLANE

DIMENSIONS: MILLIMETERS



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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